

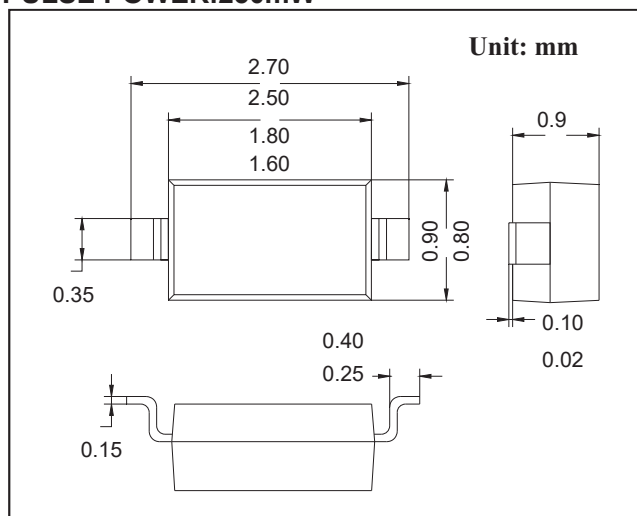
SOD-323 SCHOTTKY BARRIER DIODE

VOLTAGE RANGE: 20V-40V PEAK PULSE POWER:250mW

Low Forward Voltage Drop
Guard Ring Construction for Transient Protection
Negligible Reverse Recovery Time
Very Low Reverse Capacitance

MECHANICAL DATA

BM UÜÖEHGHÄÜ { æ||ÄU~c|ä}^ÄÜ|æ•c&ÄÜæ&\æ*^
Ü[|æ!äc ^ KÄÖ[[|!Äàæ}ä!ä^}[c^•Ä&æ@[ä^!^}ä
T[~}cä}*ÄÜ[•äcä[}KÄCE}^



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

Parameter	Symbol	B5817WS	B5818WS	B5819WS	Unit
Non-repetitive peak reverse voltage	V_{RM}	20	30	40	V
Peak repetitive peak reverse voltage	V_{RRM}				
Working peak reverse voltage	V_{RWM}	20	30	40	V
DC blocking voltage	V_R				
RMS reverse voltage	$V_{R(RMS)}$	14	21	28	V
Average rectified output current	I_O	1			A
Forward current	I_{FSM}	9			A
Repetitive peak forward current	I_{FRM}	1.5			A
Power dissipation	P_d	250			mW
Thermal resistance junction to ambient	$R_{\theta JA}$	400			°C/W
Junction temperature	T_J	125			°C
Storage temperature	T_{STG}	-55~+150			°C

Electrical Specification ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1\text{mA}$ B5817WS B5818WS B5819WS	20 30 40		V
Reverse voltage leakage current	I_R	$V_R=20\text{V}$ $V_R=30\text{V}$ $V_R=40\text{V}$ B5817WS B5818WS B5819WS		1	mA
Forward voltage	V_F	B5817WS $I_F=1\text{A}$ $I_F=3\text{A}$		0.45 0.75	V
		B5818WS $I_F=1\text{A}$ $I_F=3\text{A}$		0.55 0.875	V
		B5819WS $I_F=1\text{A}$ $I_F=3\text{A}$		0.6 0.9	V
Diode capacitance	C_D	$V_R=4\text{V}$, $f=1\text{MHz}$		120	pF

MARKING:

B5817WS	B5818WS	B5819WS
SJ	SK	SL

RATINGS AND CHARACTERISTIC CURVES

